

Data Sheet

September 2013

# N-Channel Power MOSFET 60V, 50A, 22 $m\Omega$

These N-Channel power MOSFETs are manufactured using the MegaFET process. This process, which uses feature sizes approaching those of LSI integrated circuits gives optimum utilization of silicon, resulting in outstanding performance. They were designed for use in applications such as switching regulators, switching converters, motor drivers, and relay drivers. These transistors can be operated directly from integrated circuits.

Formerly developmental type TA49018.

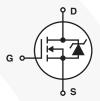
### **Ordering Information**

PART NUMBER	PACKAGE	BRAND		
RFP50N06	TO-220AB	RFP50N06		

### **Features**

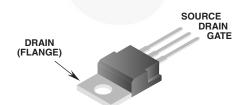
- 50A, 60V
- $r_{DS(ON)} = 0.022\Omega$
- Temperature Compensating PSPICE<sup>®</sup> Model
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- 175°C Operating Temperature

### Symbol



### **Packaging**

JEDEC TO-220AB



### **RFP50N06**

### **Absolute Maximum Ratings** $T_C = 25^{\circ}C$ , Unless Otherwise Specified

	RFP50N06	UNITS
Drain to Source Voltage (Note 1)	60	V
Drain to Gate Voltage ( $R_{GS} = 20k\Omega$ ) (Note 1) $V_{DGR}$	60	V
Gate to Source Voltage	±20	V
Continuous Drain Current (Figure 2)	50 (Figure 5)	Α
Pulsed Avalanche RatingE <sub>AS</sub>	(Figure 6)	
Power Dissipation	131 0.877	W/°C
Operating and Storage Temperature	-55 to 175	°C
Maximum Temperature for Soldering  Leads at 0.063in (1.6mm) from Case for 10s	300 260	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

#### NOTE

1.  $T_J = 25^{\circ}C$  to  $150^{\circ}C$ .

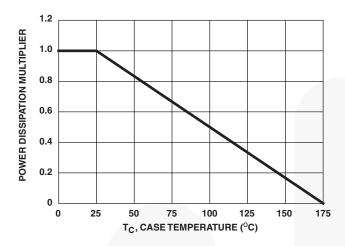
### $\textbf{Electrical Specifications} \hspace{0.3cm} \textbf{T}_{C} = 25^{o}\text{C}, \hspace{0.3cm} \textbf{Unless Otherwise Specified}$

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV <sub>DSS</sub>	$I_D = 250\mu A, V_{GS} = 0V \text{ (Figure 11)}$		60	-	-	V
Gate to Source Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_D = 250 \mu A \text{ (Figure 10)}$		2	-	4	V
Zero Gate Voltage Drain Current	ro Gate Voltage Drain Current $I_{DSS}$ $V_{DS} = 60V$ , $V_{GS} = 0V$ $T_{C} = 25^{\circ}C$		$T_{C} = 25^{\circ}C$	-\	-	1	μА
		$T_{C} = 150^{\circ}C$	-	-	50	μА	
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V		-	-	±100	nA
Drain to Source On Resistance	r <sub>DS(ON)</sub>	I <sub>D</sub> = 50A, V <sub>GS</sub> = 1	0V (Figures 9)	-	-	0.022	Ω
Turn-On Time	ton	$V_{DD} = 30V$ , $I_{D} = 50A$ $R_{L} = 0.6\Omega$ , $V_{GS} = 10V$ $R_{GS} = 3.6\Omega$ (Figure 13)		-	-	95	ns
Turn-On Delay Time	t <sub>d(ON)</sub>			-	12	-	ns
Rise Time	t <sub>r</sub>			-	55	-	ns
Turn-Off Delay Time	t <sub>d(OFF)</sub>			-	37	-	ns
Fall Time	t <sub>f</sub>			/-	13	- 1	ns
Turn-Off Time	tOFF			-	-	75	ns
Total Gate Charge	Q <sub>g(TOT)</sub>	V <sub>GS</sub> = 0 to 20V		-	125	150	nC
Gate Charge at 10V	Q <sub>g(10)</sub>	$\begin{aligned} &V_{GS} = 0 \text{ to } 10V \\ &V_{GS} = 0 \text{ to } 2V \end{aligned} \begin{vmatrix} R_L = 0.96\Omega \\ I_{g(REF)} = 1.45\text{mA} \\ \text{(Figure 13)} \end{aligned}$		-	67	80	nC
Threshold Gate Charge	Q <sub>g(TH)</sub>			-	3.7	4.5	nC
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1MHz (Figure 12)		-	2020	-	pF
Output Capacitance	C <sub>OSS</sub>			-	600	-	pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			-	200	//	pF
Thermal Resistance Junction to Case	$R_{ heta JC}$	(Figure 3)		-	-	1.14	°C/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	TO-220		-	-	62	°C/W
		-		-	-	-	-

### **Source to Drain Diode Specifications**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	$V_{SD}$	I <sub>SD</sub> = 50A	-	-	1.5	V
Reverse Recovery Time	t <sub>rr</sub>	$I_{SD} = 50A$ , $dI_{SD}/dt = 100A/\mu s$	-	-	125	ns

### Typical Performance Curves Unless Otherwise Specified



60 50 40 30 20 10 0 25 50 75 100 125 150 175 T<sub>C</sub>, CASE TEMPERATURE (°C)

FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

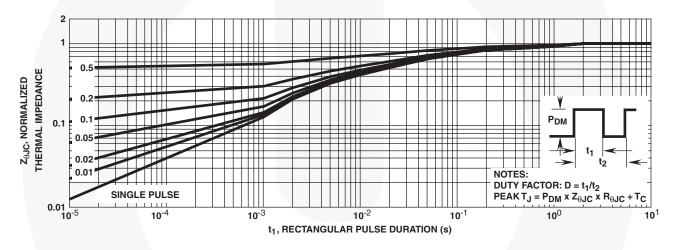


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

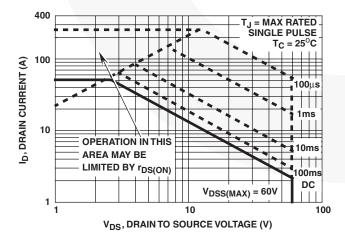


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

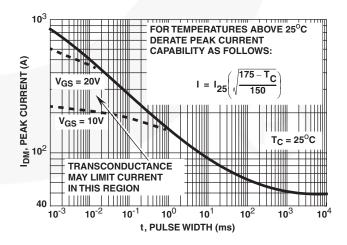
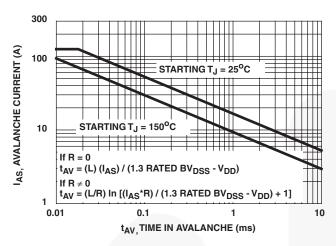


FIGURE 5. PEAK CURRENT CAPABILITY

### Typical Performance Curves Unless Otherwise Specified (Continued)



NOTE: Refer to Fairchild Application Notes 9321 and 9322.

#### FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING CAPABILITY

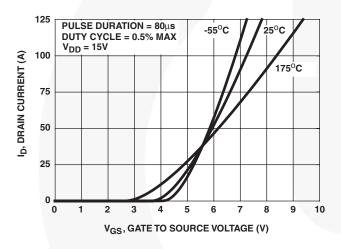


FIGURE 8. TRANSFER CHARACTERISTICS

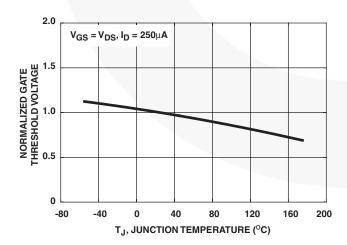


FIGURE 10. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

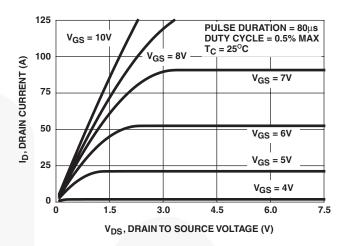


FIGURE 7. SATURATION CHARACTERISTICS

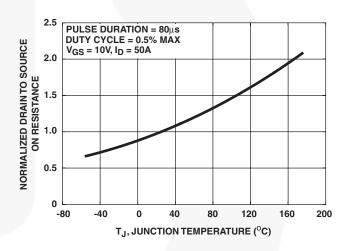


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

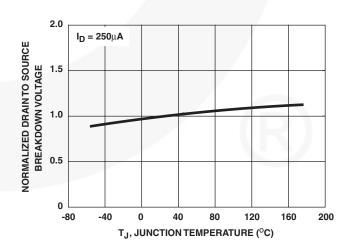


FIGURE 11. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

### Typical Performance Curves Unless Otherwise Specified (Continued)

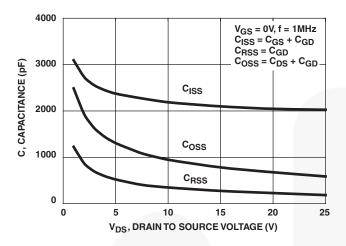
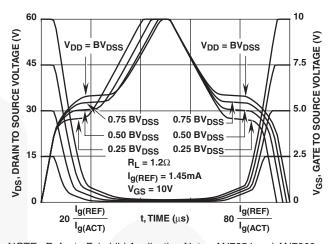


FIGURE 12. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 13. NORMALIZED SWITCHING WAVEFORMS FOR

CONSTANT GATE CURRENT

### Test Circuits and Waveforms

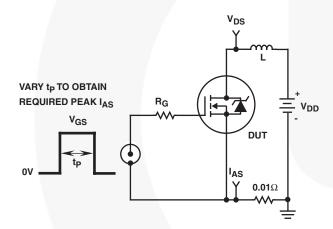


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

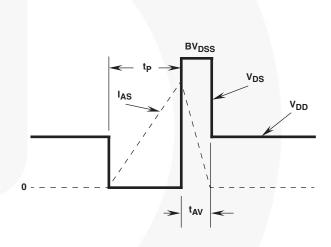


FIGURE 15. UNCLAMPED ENERGY WAVEFORMS

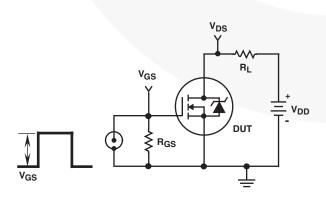


FIGURE 16. SWITCHING TIME TEST CIRCUIT

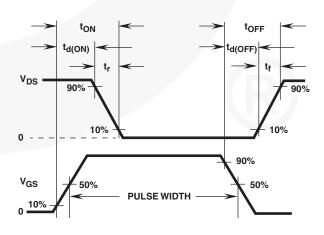


FIGURE 17. SWITCHING WAVEFORMS

## Test Circuits and Waveforms (Continued)

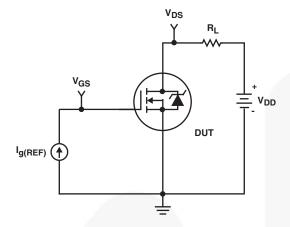


FIGURE 18. GATE CHARGE TEST CIRCUIT

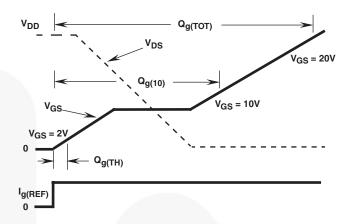


FIGURE 19. GATE CHARGE WAVEFORMS

#### **PSPICE Electrical Model**

SUBCKT RFP50N06 2 1 3

REV 2/22/93

\*NOM TEMP = 25°C

CA 12 8 3.68e-9 CB 15 14 3.625e-9 CIN 6 8 1.98e-9

DBODY 7 5 DBDMOD DBREAK 5 11DBKMOD DPLCAP 10 5 DPLCAPMOD

EBREAK 11 7 17 18 64.59 EDS 14 8 5 8 1 EGS 13 8 6 8 1 ESG 6 10 6 8 1 EVTO 20 6 18 8 1

IT 8 17 1

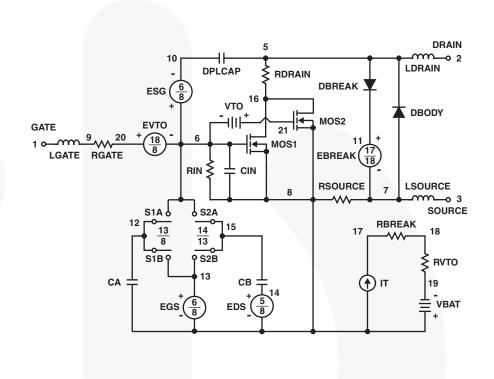
LDRAIN 2 5 1e-9 LGATE 1 9 5.65e-9 LSOURCE 3 7 4.13e-9

MOS1 16 6 8 8 MOSMOD M=0.99 MOS2 16 21 8 8 MOSMOD M=0.01

RBREAK 17 18 RBKMOD 1 RDRAIN 5 16 RDSMOD 1e-4 RGATE 9 20 0.690 RIN 6 8 1e9 RSOURCE 8 7 RDSMOD 12e-3 RVTO 18 19 RVTOMOD 1

S1A 6 12 13 8 S1AMOD S1B 13 12 13 8 S1BMOD S2A 6 15 14 13 S2AMOD S2B 13 15 14 13 S2BMOD

VBAT 8 19 DC 1 VTO 21 6 0.678



.MODEL DBDMOD D (IS=9.85e-13 RS=4.91e-3 TRS1=2.07e-3 TRS2=2.51e-7 CJO=2.05e-9 TT=4.33e-8)

.MODEL DBKMOD D (RS=1.98e-1 TRS1=2.35E-4 TRS2=-3.83e-6)

.MODEL DPLCAPMOD D (CJO=1.42e-9 IS=1e-30 N=10)

.MODEL MOSMOD NMOS (VTO=3.65 KP=35 IS=1e-30 N=10 TOX=1 L=1u W=1u)

.MODEL RBKMOD RES (TC1=1.23e-3 TC2=-2.34e-7)

.MODEL RDSMOD RES (TC1=5.01e-3 TC2=1.49e-5)

.MODEL RVTOMOD RES (TC1=-5.03e-3 TC2=-5.16e-6)

.MODEL S1AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-6.75 VOFF=-2.5)

.MODEL S1BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-2.5 VOFF=-6.75)

.MODEL S2AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-2.7 VOFF=2.3)

.MODEL S2BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=2.3 VOFF=-2.7)

.ENDS

NOTE: For further discussion of the PSPICE model consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options;** authors, William J. Hepp and C. Frank Wheatley.





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